

Low Consumption Power Class D Amplifier

9W+9W Analog Input Class D Speaker Amplifier

BD28411MUV

General Description

BD28411MUV is 9W+9W stereo class D amplifier which does not require an external heat sink.

This IC is incorporated with a precise oscillator to generate multiple switching frequencies that can avoid the AM radio interference. In addition, 2.1Ch audio system can be realized by master and slave operation without beat noise caused by interference between two ICs. Furthermore, this IC realizes lower power consumption during small power output, so this product is most suitable for battery equipped speaker systems such as wireless speakers.

Features

- Analog Differential Input
- Low Standby Current
- Output Feedback Circuitry prevents sound quality degradation caused by power supply voltage fluctuation, achieves low noise and low distortion, eliminates the need of large electrolytic-capacitors for decoupling.
- Power limit function (Linearly-programmable)
- Selectable switching frequency (AM avoidance function)
- Synchronization control is supported (Selectable Master and Slave operation)
- Parallel BTL (PBTL) is supported
- Wide voltage range (V_{CC}=4.5V to 13V)
- High efficiency and low-heat-generation make the system smaller, thinner, and more power-saving
- Pop noise prevention during power supply ON/OFF
- High reliability design by built-in protection circuits
 - Overheat protection
 - Under voltage protection
 - Output short protection
 - Output DC voltage protection
- Small package (VQFN032V5050) achieves mount area reduction

Applications

Wireless speaker, Small active speaker, Portable audio equipment, etc.

Key Specifications

■ Supply Voltage Range: 4.5V to 13V ■ Speaker Output Power: 9W+9W (Typ)

 $(V_{CC}=12V, R_L=8\Omega, PLIMIT=0V)$

■ Total Harmonic Distortion Ratio:

Operating Temperature Range:

0.03% (Typ) @Po=1W (V_{CC}=11V, R_L=8 Ω , PLIMIT=0V)

■ Crosstalk: 100dB (Typ)
 ■ PSRR: 55dB (Typ)
 ■ Output Noise Voltage: -80dBV (Typ)

Standby Current: 0.1µA (Typ)

Operating Current: 16mA (Typ)
(No load or filter, No signal)

Package

 $W(Typ) \times D(Typ) \times H(Max)$

-25°C to +85°C



Typical Application Circuit

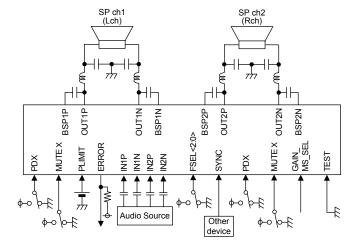


Figure 1. Typical Application Circuit

Pin Configuration

(TOP VIEW)

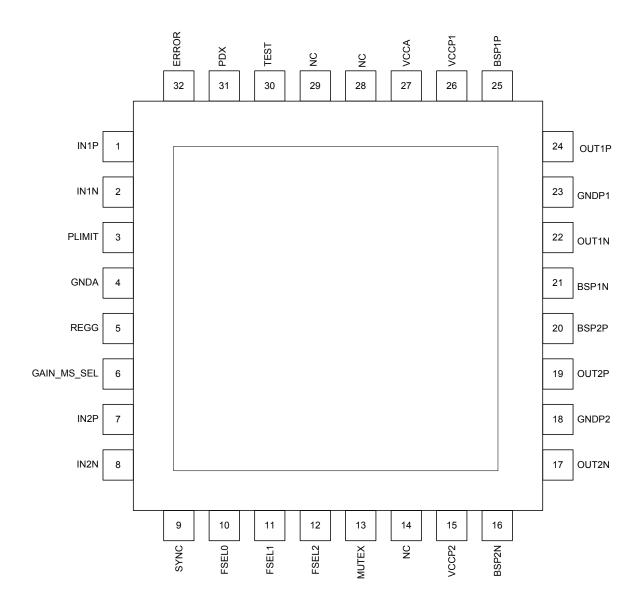


Figure 2. Pin Configuration

Pin Description

Pin No.	Pin Name	Ю	Function	Internal Equivalent Circuit
1	IN1P	I	Positive input pin for Ch1	1
2	IN1N	I	Negative input pin for Ch1	2
3	PLIMIT	I	Power limit level setting pin	3 100k 100k
4	GNDA	-	GND pin for Analog signal	
5	REGG	Ο	Internal power supply pin for Gate driver Please connect a capacitor. *The REGG terminal of BD28411MUV should not be used as external supply. Therefore, do not connect anything except the capacitor for stabilization and the resistors for setting of GAIN_MS_SEL and PLIMIT.	500
6	GAIN_MS_SEL	I	Gain and Master/Slave mode Setting pin	6
7	IN2P	I	Positive input pin for Ch2	7
8	IN2N	I	Negative input pin for Ch2	8 4
9	SYNC	I/O	Clock input/output pin to synchronize multiple class D amplifiers	9 100k

Pin Description - continued

10	FSEL0	I	PWM frequency setting pin	10 100k
11	FSEL1	I	PWM frequency setting pin	5 11 100k
12	FSEL2	ı	PWM frequency setting pin	12,13
13	MUTEX	I	Speaker output mute control pin H: Mute OFF L: Mute ON	100k
14	NC	-	Non connection	
15	VCCP2	-	Power supply pin for Ch2 PWM signal Please connect a capacitor.	15
16	BSP2N	0	Boot-strap pin of Ch2 negative PWM signal Please connect a capacitor.	5
17	OUT2N	0	Output pin of Ch2 negative PWM signal Please connect to output LPF.	16, 20
18	GNDP2	_	GND pin for Ch2 PWM signal	17, 19
19	OUT2P	0	Output pin of Ch2 positive PWM signal Please connect to output LPF.	
20	BSP2P	0	Boot-strap pin of Ch2 positive PWM signal Please connect a capacitor.	18
21	BSP1N	0	Boot-strap pin of Ch1 negative PWM signal Please connect a capacitor.	26
22	OUT1N	0	Output pin of Ch1 negative PWM signal Please connect to output LPF.	21, 25
23	GNDP1	-	GND pin for Ch1 PWM signal	
24	OUT1P	0	Output pin of Ch1 positive PWM signal Please connect to output LPF.	22, 24
25	BSP1P	0	Boot-strap pin of Ch1 positive PWM signal Please connect a capacitor.	+
26	VCCP1	-	Power supply pin for Ch1 PWM signal Please connect a capacitor.	23
27	VCCA	-	Power supply pin for Analog signal Please connect a capacitor.	
28	NC	-	Non connection	
29	NC	-	Non connection	
30	TEST	I	Test pin Please connect to GND.	30 100k

Pin Description - continued

31	PDX	I	Power down setting pin H: Active L: Standby	55k 31 45k
32	ERROR	0	Error flag pin Please connect to pull-up resistor. H: Normal L: Error detected *An error flag is outputted when Output Short Protection, DC Voltage Protection, and High Temperature Protection are operated. This flag shows IC condition during operation.	500

The numerical value of internal equivalent circuit is typical value, not guaranteed value.

Block Diagram

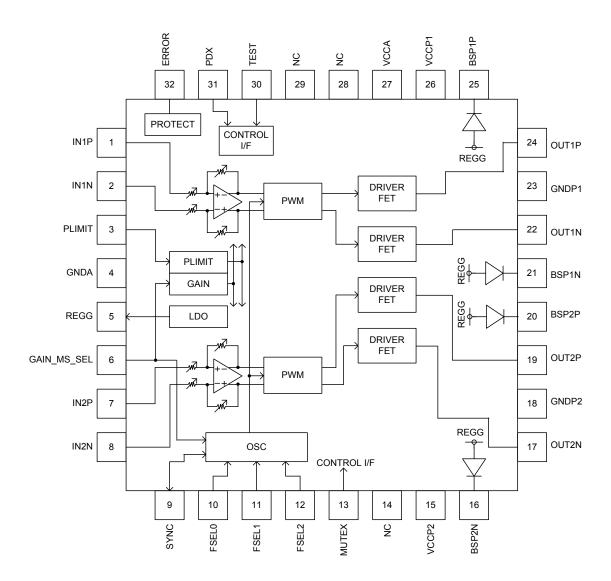


Figure 3. Block Diagram

Absolute Maximum Ratings (Ta = 25°C)

3				
Parameter	Symbol	Rating	Unit	Applied pins and Conditions
Supply Voltage ^(Note 1)	V _{CCMAX}	-0.3 to +15.5	V	VCCA,VCCP1,VCCP2
Davis Diagram (Note 2)	D4	3.26 ^(Note 3)	W	Diagram of the David Diagram of the data its
Power Dissipation ^(Note 2)	Pd	4.56 ^(Note 4)	W	Please refer to Power Dissipation for details.
Input Voltage1 ^(Note 1)	V _{IN}	-0.3 to +V _{REGG}	V	IN1P, IN1N, IN2P, IN2N, PLIMIT, GAIN_MS_SEL, PLIMIT, SYNC ^(Note 5) , FSEL0, FSEL1, FSEL2, PDX, MUTEX
Input Voltage2(Note 1)	V _{ERR}	-0.3 to +7	V	ERROR
Pin Voltage1 ^{(Note 1) (Note 6)}	V _{PIN1}	-0.3 to +V _{CCMAX}	V	OUT1P, OUT1N, OUT2P, OUT2N
Operating Temperature	Topr	-25 to +85	°C	
Storage Temperature	Tstg	-55 to +150	°C	
Junction Temperature	Tjmax	+150	°C	

- The voltage that can be applied reference to GND (Pin4, 18, 23). Do not exceed Pd and Tjmax=150°C. (Note 1)
- (Note 2)
- Derate by 26.1mW/°C for operating above Ta=25°C when mounted on 74.2mm \times 74.2mm \times 1.6mm, FR4, 4-layer glass epoxy board (Note 3)
- (Top and bottom layer back copper foil size: 20.2mm², 2nd and 3rd layer back copper foil size: 5505mm²). There are thermal vias on the board. (Note 4) Derate by 36.5mW/°C for operating above Ta=25°C when mounted on 74.2mm × 74.2mm × 1.6mm, FR4, 4-layer glass epoxy board
- (Copper area: 5505mm²). There are thermal vias on the board.
- (Note 5) SYNC pin is I/O pin. It is specified for input mode.
- (Note 6) Please use under this rating including the AC peak waveform (overshoot) for all conditions. Only undershoot is allowed at condition of ≤ 15.5V by the VCC reference and ≤ 10nsec (cf. Figure 4)

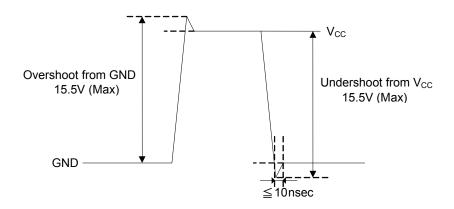


Figure 4. Overshoot and Undershoot

Caution: Operating the IC over the absolute maximum ratings may damage the IC. The damage can either be a short circuit between pins or an open circuit between pins and the internal circuitry. Therefore, it is important to consider circuit protection measures, such as adding a fuse, in case the IC is operated over the absolute maximum ratings.

Recommended Operating Conditions (Ta= -25°C to +85°C)

Parameter	Symbol	Min	Тур	Max	Unit	Applied pins and Conditions
Supply Voltage	V _{IN}	4.5	-	13	V	VCCA, VCCP1, VCCP2
Minimum Load Impedance ^(Note 7)	R _{L1}	5.4	-	-	Ω	BTL
Millimum Load impedance	R _{L2}	3.2	-	-	Ω	PBTL
High Level Input Voltage	V _{IH}	2.0	-	-	V	FSEL0, FSEL1, FSEL2, MUTEX, PDX
Low Level Input Voltage	V _{IL}	0	-	0.8	V	FSEL0, FSEL1, FSEL2, MUTEX, PDX
Low Level Output Voltage	V_{OL}	-	-	0.8	V	ERROR, I _{OL} =0.5mA

(Note 7) Pd should not be exceeded.

Electrical Characteristics

(Unless otherwise specified, Ta=25°C, V_{CC} =11V, f_{PWM} =600kHz, f_{IN} =1kHz, R_L =8 Ω , PDX=3.3V, MUTEX=3.3V, PLIMT=0V, Gain=26dB, Output LC filter: L=15 μ H, C=1 μ F

when V_{CC} >11V, snubber circuit is added: C=680pF, R=5.6 Ω)

Parameter	Symbol	Min	Тур	Max	Unit	Applied pins and Conditions
Quiescent Standby Current	I _{CC1}	-	0.1	25	μΑ	No load or filter, PDX=L, MUTEX=L
Quiescent Mute Current	I _{CC2}	-	10	20	mA	No load or filter, PDX=H, MUTEX=L
Quiescent Operating Current	I _{CC3}	-	16	32	mA	No load or filter, No signal, PDX=H, MUTEX=H
Regulator Output Voltage	V_{REGG}	4.45	5.55	6.05	V	PDX=H, MUTEX=H
Input Pull Down Impedance 1	R _{IN1}	70	100	130	kΩ	MUTEX, PDX, FSEL0, FSEL1, FSEL2, SYNC(Slave mode only),
Input Pull Down Impedance 2	R _{IN2}	140	200	260	kΩ	PLIMIT
Output Power ^(Note 8)	P ₀₁	-	9	-	W	V _{CC} =12V, THD+N=10%
Gain 1 ^(Note 8)	G _{V1}	19	20	21	dB	Po=1W, GAIN_MS_SEL= 0V
Gain 2 ^(Note 8)	G _{V2}	25	26	27	dB	P _O =1W , GAIN_MS_SEL= 2/9 × V _{REGG}
Gain 3 ^(Note 8)	G _{V3}	31	32	33	dB	P _O =1W, GAIN_MS_SEL= 3/9 × V _{REGG}
Gain 4 ^(Note 8)	G _{V4}	35	36	37	dB	P _O =1W, GAIN_MS_SEL= 4/9 × V _{REGG}
Total Harmonic Distortion ^(Note 8)	THD	-	0.03	-	%	Po=1W, BW=20 to 20kHz (AES17)
Crosstalk ^(Note 8)	CT	60	100	-	dB	Po=1W, 1kHz BPF
PSRR ^(Note 8)	PSRR	-	55	-	dB	V _{ripple} =0.2 V _{P-P} , f=1kHz
Output Noise Level ^(Note 8)	V_{NO}	-	-80	-70	dBV	Po=0W, BW=IHF-A
	f _{PWM1}	564	600	636	kHz	FSEL2=H, FSEL1=L, FSEL0=H
PWM (Pulse Width Modulation) Frequency	f _{PWM2}	470	500	530	kHz	FSEL2=H, FSEL1=L, FSEL0=L
(Alata 0). The value is presified as twice level	f _{PWM3}	376	400	424	kHz	FSEL2=L, FSEL1=H, FSEL0=H

(Note 8) The value is specified as typical application. Actual value depends on PCB layout and external components.

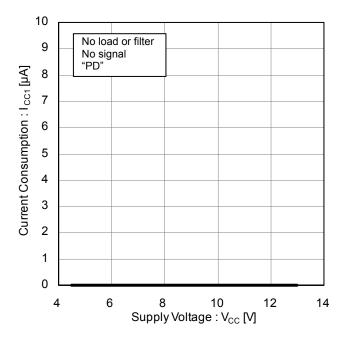


Figure 5. Circuit Current vs Supply Voltage (PD)

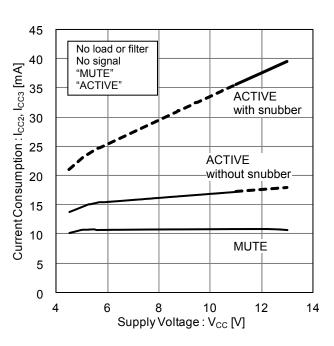


Figure 6. Circuit Current vs Supply Voltage (MUTE, ACTIVE)

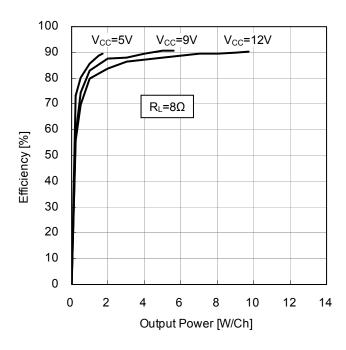


Figure 7. Efficiency vs Output Power $(R_L=8\Omega)$

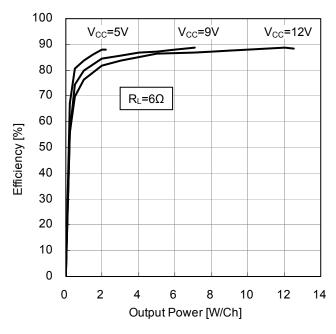


Figure 8. Efficiency vs Output Power $(R_L=6\Omega)$

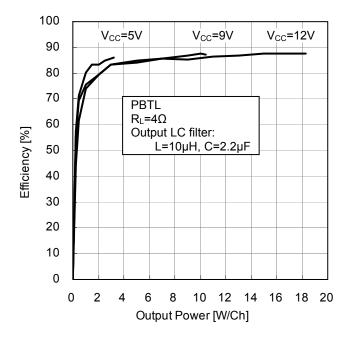


Figure 9. Efficiency vs Output Power (PBTL, R_L =4 Ω)

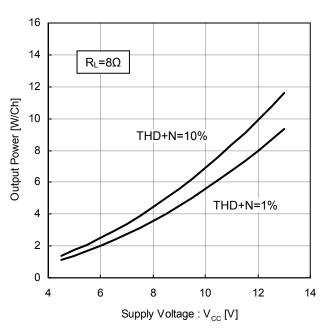


Figure 10. Output Power vs Supply Voltage $(R_L=8\Omega)$

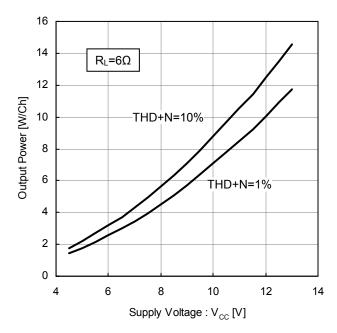


Figure 11. Output Power vs Supply Voltage $(R_L=6\Omega)$

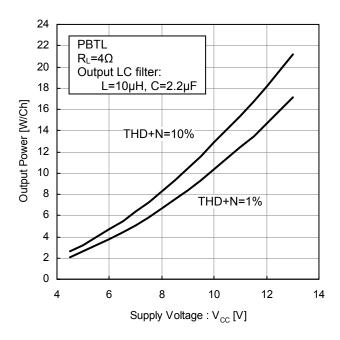


Figure 12. Output Power vs Supply Voltage (PBTL, R_L =4 Ω)

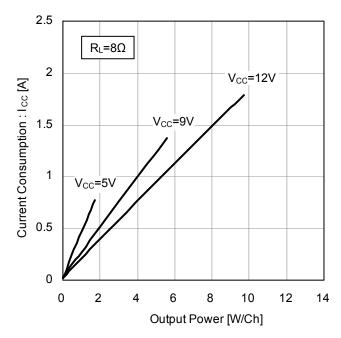


Figure 13. Circuit Current vs Output Power $(R_L=8\Omega)$

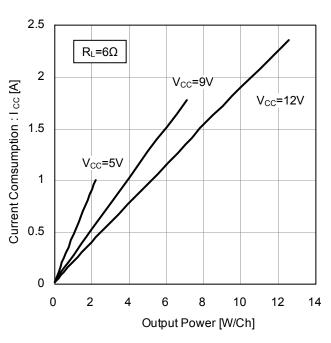


Figure 14. Circuit Current vs Output Power $(R_L=6\Omega)$

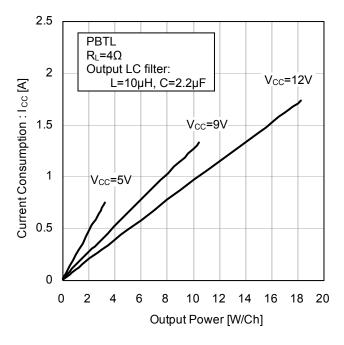


Figure 15. Circuit Current vs Output Power (PBTL, R_L =4 Ω)

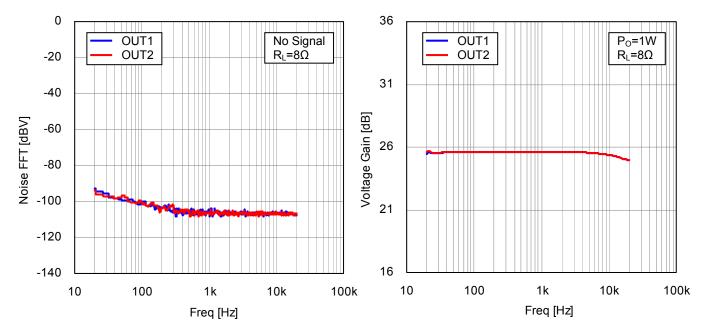
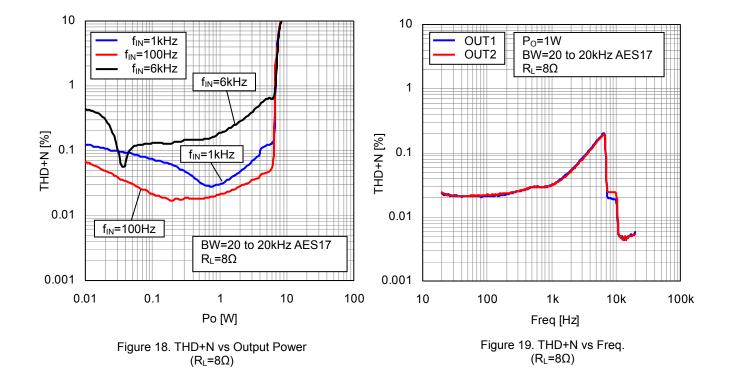


Figure 16. FFT of Output Noise Voltage $(R_L=8\Omega)$

Figure 17. Voltage Gain vs Freq. $(R_L=8\Omega)$



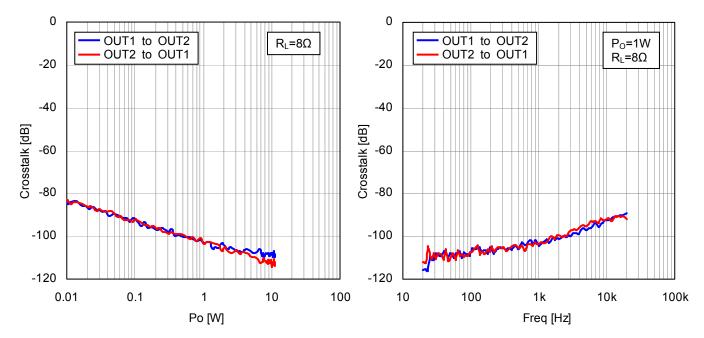


Figure 20. Crosstalk vs Output Power $(R_L=8\Omega)$

Figure 21. Crosstalk vs Freq. $(R_L=8\Omega)$

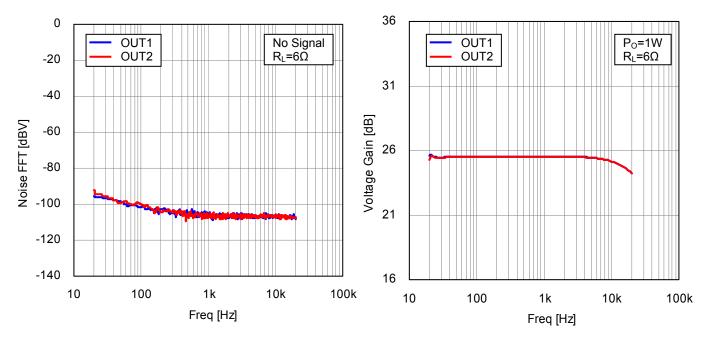
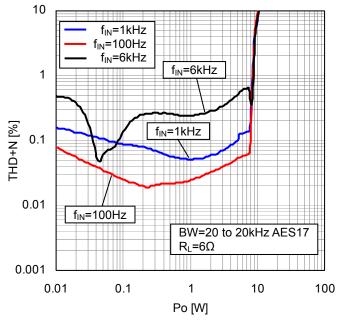


Figure 22. FFT of Output Noise Voltage $(R_L$ =6 $\Omega)$

Figure 23. Voltage Gain vs Freq. $(R_L=6\Omega)$

(Unless otherwise specified, Ta=25°C, V_{CC} =11V, f_{PWM} =600kHz, f_{IN} =1kHz, R_L =8 Ω , PDX=3.3V, MUTEX=3.3V, PLIMT=0V, Gain=26dB, Output LC filter: L=15 μ H, C=1 μ F when V_{CC} >11V, snubber circuit is added: C=680pF, R=5.6 Ω)

10



OUT1 Po=1W OUT2 BW=20 to 20kHz AES17 $R_L=6\Omega$ 1 THD+N [%] 0.1 0.01 0.001 10 100 1k 10k 100k Freq [Hz]

Figure 24. THD+N vs Output Power $(R_L=6\Omega)$

Figure 25. THD+N vs Freq. $(R_L=6\Omega)$

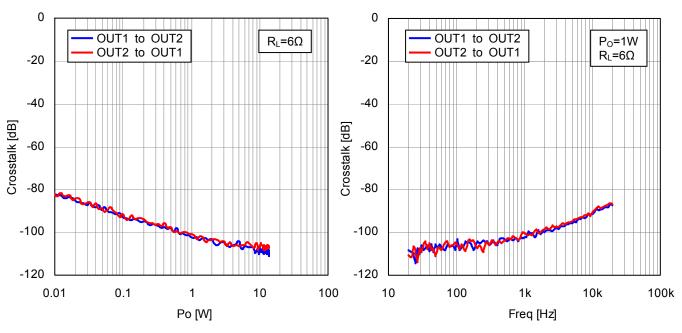


Figure 26. Crosstalk vs Output Power $(R_L=6\Omega)$

Figure 27. Crosstalk vs Freq. $(R_L=6\Omega)$

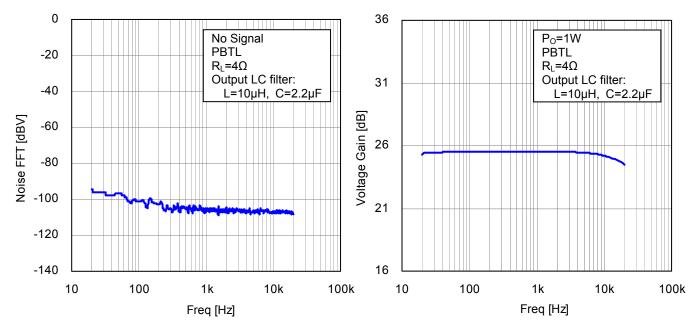
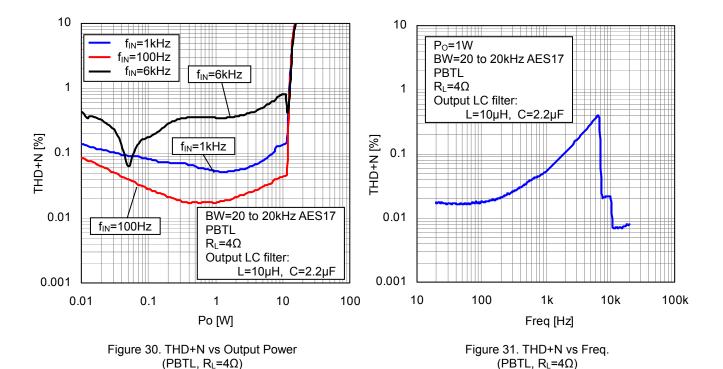


Figure 28. FFT of Output Noise Voltage (PBTL, R_L =4 Ω)

Figure 29. Voltage Gain vs Freq. (PBTL, R_L =4 Ω)



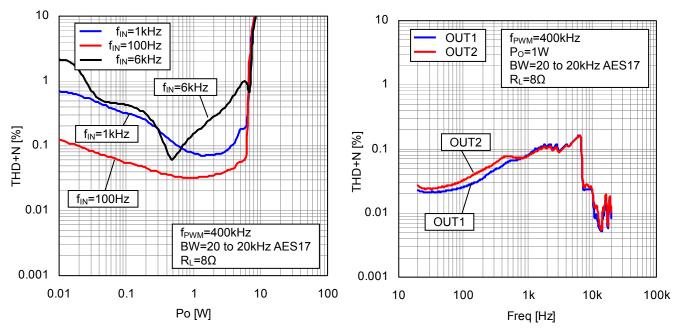


Figure 32. THD+N vs Output Power $(f_{PWM}=400kHz, R_L=8\Omega)$

Figure 33. THD+N vs Freq. $(f_{PWM}=400kHz, R_L=8\Omega)$

Power up / down sequence

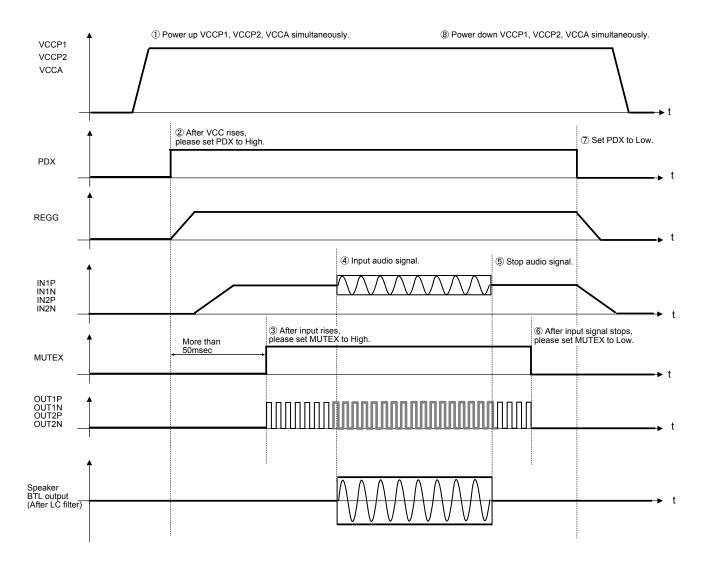


Figure 34. Power Up / Down Sequence

Function Description

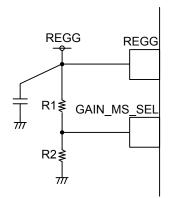
(1) Power down and Mute setting

		7				
		Norm	al	ERROR Detection		
PDX	MUTEX	PWM output	ERROR ^(Note 10)	PWM output	ERROR ^(Note 10)	
		OUT1P, 1N, 2P, 2N	ERROR	OUT1P, 1N, 2P, 2N	ERROR	
ı	L/H	High-Z_Low ^(Note 9)	Ц	High-Z_Low ^(Note 9)	Ц	
L	ЦП	(Power down)	17	(Power down)	11	
Н		High-Z_Low ^(Noté 9)	Н	High-Z_Low ^(Note 9)		
П	L	(MUTE_ON)	п	(MUTE_ON)	L	
ш	Ш	Active	Ш	High-Z_Low ^(Note 9)	1	
П	П	(MUTE_OFF)	П	(MUTE_ON)	L	

(Note 9) All power transistors are OFF and output terminals are pulled down by $40k\Omega$ (Typ). (Note 10) ERROR pin is pulled up by $10k\Omega$ resistor.

(2) Gain and Master/Slave setting

Master/slave and gain are set by GAIN_MS_SEL pin voltage.



R1 ^(Note 11) (to REGG)	R2 ^(Note 11) (to GND)	Master/Slave	Gain	Input Impedance
18kΩ	Open	Slave	36dB	30kΩ
18kΩ	68kΩ	Slave	32dB	45.1kΩ
33kΩ	68kΩ	Slave	26dB	79.3kΩ
51kΩ	68kΩ	Slave	20dB	127.9kΩ
68kΩ	51kΩ	Master	36dB	30kΩ
68kΩ	33kΩ	Master	32dB	45.1kΩ
68kΩ	18kΩ	Master	26dB	79.3kΩ
open	18kO	Master	20dB	127.9kO

(Note 11) Please use 1% tolerance resistor.

Figure 35. GAIN_MS_SEL Pin Setting

Setting cannot be changed when IC is active, but it can be set by rebooting (PDX=H to L to H).

Master/Slave Function

This IC has master and slave mode, and it can be synchronized by PWM frequency between two ICs. In master mode, SYNC pin becomes output pin for synchronization and in slave mode it becomes input pin, so please connect each SYNC pins. Please set FSEL2/FSEL1/FSEL0 pins to be same each other.

(3) Parallel BTL Function

Parallel BTL mode can be set by connecting IN2P and IN2N pins to GND. Please short OUT1P – OUT2P, OUT1N – OUT2N near the IC as much as possible. Parallel BTL mode cannot be set by connecting IN1P and IN1N pins to GND.

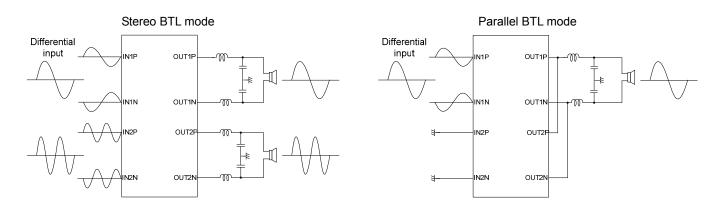
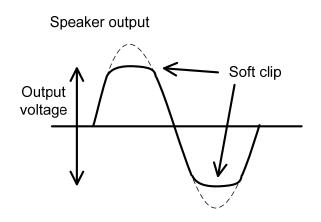


Figure 36. Parallel BTL mode

(4) Power Limit Function

It is possible to limit the maximum output voltage by PLIMIT pin.



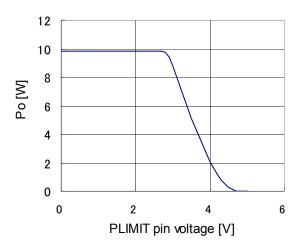


Figure 37. Power Limit

Figure 38. Power Limit Function [V_{CC} =12V, R_L =8 Ω] (Typ)

Ex.) If PLIMIT is set by R3A=12k Ω and R3B=20k Ω in "Application Information", output power is limited to about 6.4W.

If power limit function is not needed, connect PLIMIT pin to GND.

(5) FSEL2 / FSEL1 / FSEL0 (AM avoidance function)

FSEL2 / FSEL1 / FSEL0 pins are used for PWM frequency setting. PWM frequency is near to AM radio frequency band therefore this makes interference during AM radio is used, and may negatively affects reception of AM radio wave. This interference can be reduced by shift of PWM frequency. Below are the recommended settings. For example, receiving AM radio wave of 1269kHz in Asia / Europe please set PWM frequency to 500kHz.

AM freque	ency [kHz]	Recommended PWM frequency setting			
Americas	Asia / Europe	f _{PWM} =400kHz FSEL2=L FSEL1=H FSEL0=H	f _{PWM} =500kHz FSEL2=H FSEL1=L FSEL0=L	f _{PWM} =600kHz FSEL2=H FSEL1=L FSEL0=H	
	522 – 540	0	-	0	
540 – 917	540 – 914	-	0	-	
917 – 1125	914 – 1122	0	-	0	
1125 – 1375	1122 – 1373	-	0	-	
1375 – 1547	1373 – 1548	0	-	0	
1547 – 1700	1548 – 1701	0	-	0	

Do not set following conditions:

FSEL2=FSEL1=FSEL0=H FSEL2=H, FSEL1=H, FSEL0=L FSEL2=L, FSEL1=H, FSEL0=L FSEL2=L, FSEL1=L, FSEL0=H FSEL2=FSEL1=FSEL0=L

Application Information

(1) Application Circuit Example 1 (Stereo BTL, V_{CC}=4.5 to 11V)

Overshoot of output PWM differs according to the board, and etc. Please check to ensure that it is lower than absolute maximum ratings. If it exceeds the absolute maximum ratings, snubber circuit need to be added, the circuit example is shown on the next page.

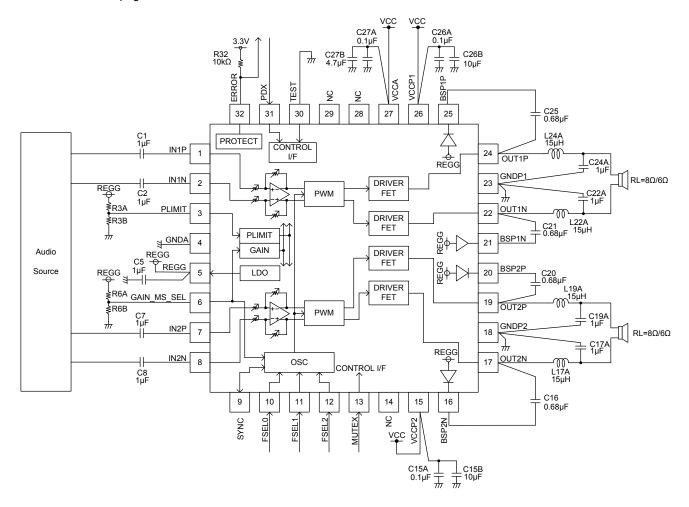


Figure 39. Application Circuit 1

BOM 1 (Stereo BTL, V_{CC}=4.5 to 11V)

BOW I (Stereo BTL, VCC-4.3 to TTV)						
Parts	Qty.	Parts No.	Description			
	1	R3A	Pof Function Description (4) Power Limit Function			
	1	R3B	Ref. Function Description (4)Power Limit Function			
Resistor	1	R6A	Def Function Description (2) Cain and Master/Clave setting			
	1	R6B	Ref. Function Description (2)Gain and Master/Slave setting			
	1	R32	100kΩ, 1/16W, J(±5%)			
	4	C1, C2, C7, C8	1μF, 16V, B(±10%)			
	1	C5 ^(Note 12)	1μF, 16V, B(±10%)			
	3	C15A, C26A, C27A ^(Note 12)	0.1µF, 25V, B(±10%)			
Capacitor	2	C15B, C26B ^(Note 12)	10µF, 25V, B(±10%)			
	4	C16, C20, C21, C25 ^(Note 12)	0.68µF, 16V, B(±10%)			
	4	C17A, C19A, C22A, C24A	1μF, 25V, B(±10%)			
	1	C27B ^(Note 12)	4.7μF, 25V, B(±10%)			
Inductor	4	L17A, L19A, L22A, L24A	15μH, 2.1A, ±20%			

(Note 12) Please place it near pin as much as possible.

(2) Application Circuit Example 2 (Stereo BTL, V_{CC} =11 to 13V) Please add the snubber circuit at OUT pin when V_{CC} =11 to 13V.

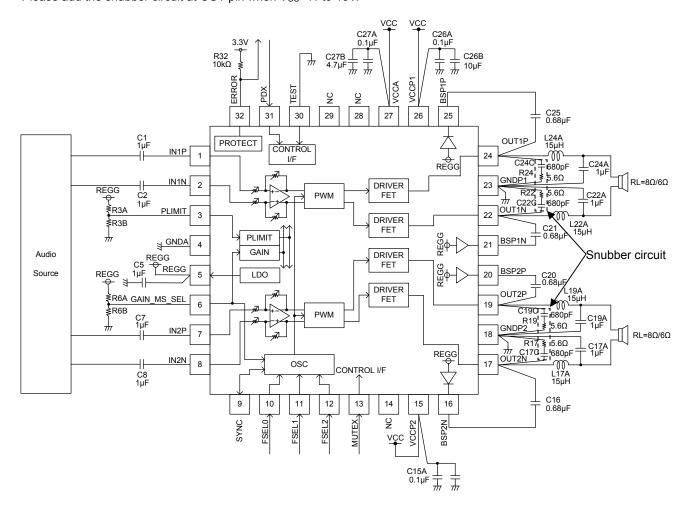


Figure 40. Application Circuit 2

BOM 2 (Stereo BTL, V_{CC}=11to 13V)

BOW 2 (Stereo BTE, VCC-11to 13V)						
Parts	Qty.	Parts No.	Description			
	1	R3A	Def Function Description (A) Dower Limit Function			
	1	R3B	Ref. Function Description (4)Power Limit Function			
Resistor	1	R6A	Ref. Function Description (2)Gain and Master/Slave setting			
Resistor	1	R6B	Ref. Pulliction Description (2)Gain and Master/Slave Setting			
	1	R32	100kΩ, 1/16W, J(±5%)			
	4	R17, R19, R22, R24	5.6Ω, 1/10W, J(±5%)			
	4	C1, C2, C7, C8	1μF, 16V, B(±10%)			
	1	C5 ^(Note 13)	1μF, 16V, B(±10%)			
	3	C15A, C26A, C27A ^(Note 13)	0.1µF, 25V, B(±10%)			
	2	C15B, C26B ^(Note 13)	10μF, 25V, B(±10%)			
Capacitor	4	C16, C20, C21, C25 ^(Note 13)	0.68µF, 16V, B(±10%)			
	4	C17A, C19A, C22A, C24A	1μF, 25V, B(±10%)			
	4	C17C, C19C, C22C,	680pF, 25V, B(±10%)			
	-	C24C ^(Note 13)	ουορί , 25 ν, Β(±10 /6)			
	1	C27B ^(Note 13)	4.7μF, 25V, B(±10%)			
Inductor	4	L17A, L19A, L22A, L24A	15μH, 2.1A, ±20%			

(Note 13) Please place it near pin as much as possible.

(3) Application Circuit Example 3 (Monaural PBTL, V_{CC}=4.5 to 11V)

Overshoot of output PWM differs according to the board, and etc. Please check to ensure that it is lower than absolute maximum ratings. If it exceeds the absolute maximum ratings, snubber circuit need to be added, the circuit example is shown on the next page.

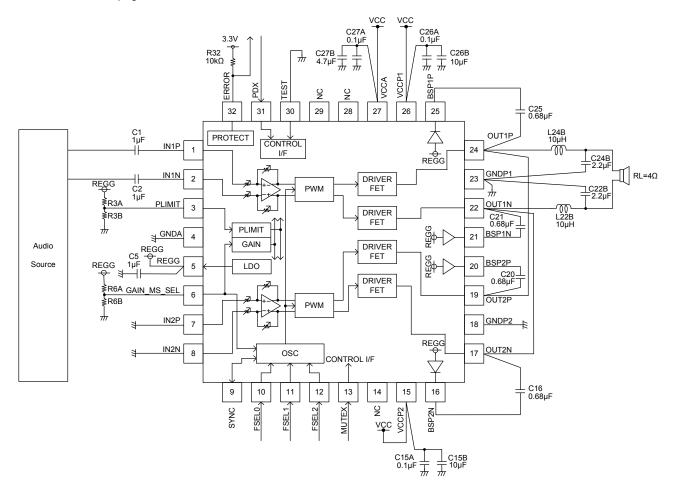


Figure 41. Application Circuit 3

BOM 3 (Monaural PBTL, V_{CC}=4.5 to 11V)

Parts	Qtv.	Parts No.	Description	
	1	R3A	Def Europies Description (A)Description	
	1	R3B	Ref. Function Description (4)Power Limit Function	
Resistor	1	R6A	Ref. Function Description (2)Gain and Master/Slave setting	
	1	R6B	Ref. Function Description (2)Gain and Master/Slave Setting	
	1	R32	100kΩ, 1/16W, J(±5%)	
	4	C1, C2, C7, C8	1μF, 16V, B(±10%)	
	1	C5 ^(Note 14)	1μF, 16V, B(±10%)	
	3	C15A, C26A, C27A ^(Note 14)	0.1μF, 25V, B(±10%)	
Capacitor	2	C15B, C26B ^(Note 14)	10µF, 25V, B(±10%)	
	4	C16, C20, C21, C25	0.68µF, 16V, B(±10%)	
	2	C22B, C24B ^(Note 14)	2.2μF, 25V, B(±10%)	
	1	C27B	4.7μF, 25V, B(±10%)	
Inductor	2	L22B, L24B	10μH, 2.6A, ±20%	

(Note 14) Please place it near pin as much as possible.

(4) Application Circuit Example 4 (Monaural PBTL, V_{CC} =11 to 13V) Please add the snubber circuit at OUT pin when V_{CC} =11 to 13V.

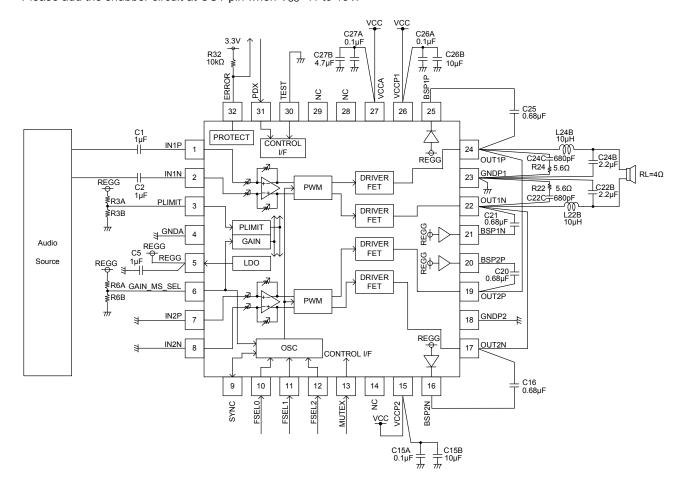


Figure 42. Application Circuit 4

BOM 4 (Monaural PBTL, Vcc=11 to 13V)

BOW 4 (Worldwar FBTE, VCC-11 to 13V)				
Parts	Qty.	Parts No.	Description	
	1	R3A	Def Function Description (4) Dewar Limit Function	
	1	R3B	Ref. Function Description (4)Power Limit Function	
Resistor	1	R6A	Pof Function Description (2) Cain and Master/Slave setting	
Resisioi	1	R6B	Ref. Function Description (2)Gain and Master/Slave setting	
	1	R32	100kΩ, 1/16W, J(±5%)	
	2	R22, R24 ^(Note 15)	5.6Ω, 1/10W, J(±5%)	
	4	C1, C2, C7, C8	1μF, 16V, B(±10%)	
	1	C5 ^(Note 15)	1μF, 16V, B(±10%)	
	3	C15A, C26A, C27A ^(Note 15)	0.1µF, 25V, B(±10%)	
Capacitar	2	C15B, C26B ^(Note 15)	10μF, 25V, B(±10%)	
Capacitor	4	C16, C20, C21, C25 ^(Note 15)	0.68µF, 16V, B(±10%)	
	2	C22B, C24B	2.2µF, 25V, B(±10%)	
	2	C22C, C24C ^(Note 15)	680pF, 25V, B(±10%)	
	1	C27B ^(Note 15)	4.7μF, 25V, B(±10%)	
Inductor	2 L22B, L24B 10µH, 2.6A, ±20%		10µH, 2.6A, ±20%	

(Note 15) Please place it near pin as much as possible.

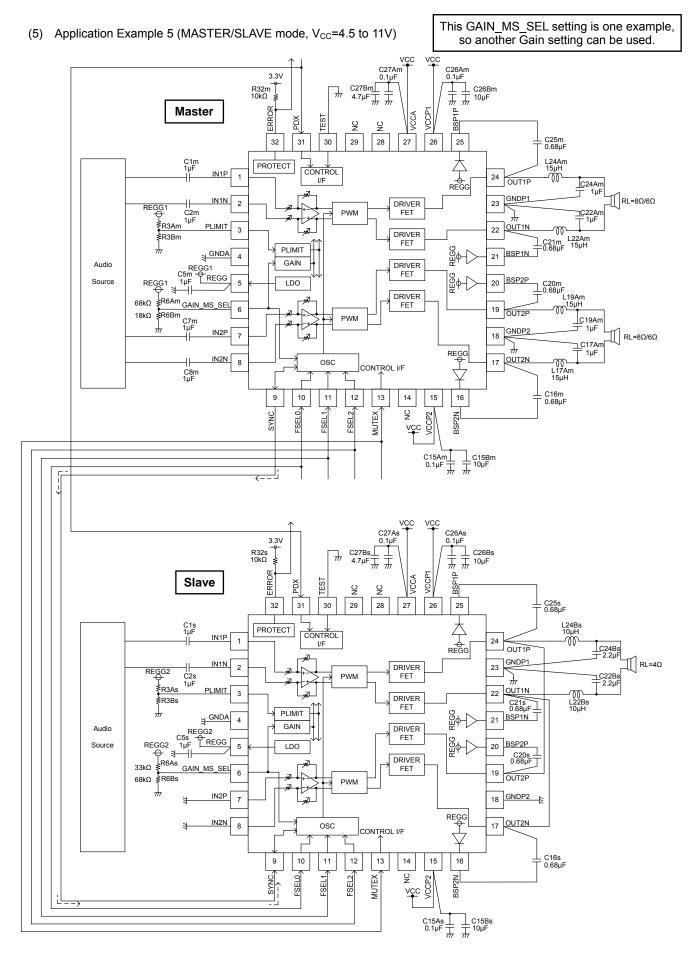


Figure 43. Application Circuit 5

About the Protection Function

Protection Function		Detecting & Releasing Condition	PWM Output OUT1P, 1N, 2P, 2N	ERROR ^(Note 16)	
Output short protection	Detecting condition	Detecting current = 8A (Typ)	High-Z_Low (Latch) ^(Note17)	L (Latch) ^(Note17)	
DC voltage protection			High-Z_Low (Latch) ^(Note17)	L (Latch) ^(Note17)	
Overheat protection	Detecting condition	Chip temperature to be over 150°C (Typ)	High-Z_Low	1	
	Releasing condition	Chip temperature to be below 120°C (Typ)	Normal operation		
Under voltage	Detecting condition	Power supply voltage to be below 4.0V (Typ)	High-Z_Low	Н	
protection	Releasing condition	Power supply voltage to be above 4.1V (Typ)	Normal operation		

⁽Note 16) ERROR pin is pulled up by 10kΩ resistor.
(Note 17) Once an IC is latched, the circuit is not released automatically even after an abnormal status is gone. The following procedures ① or ② is available for recovery.

After turning MUTEX terminal to Low (holding time to Low = 10msec (Min)) turn back to High again.
 Restore power supply after dropping to power supply voltage V_{cc} < 3V (10msec (Min) holding) which internal power on reset circuit activates.

(1) Output Short Protection (short to the power supply)

This IC has the PWM output short protection circuit that stops the PWM output when the output speaker (after LC-filter) is short-circuited to the power supply due to abnormality.

- Detecting condition It will detect when MUTEX pin is set High and the current that flows into the PWM output pin becomes 8A(Typ) or more. If detected, the PWM output instantaneously goes to the state of High-Z_Low and IC is latch.
- Releasing method ① After turning MUTEX terminal to Low(holding time to Low = 10msec(Min)) turn back to High again.
 - ② Restore power supply after the voltage dropped to internal power on reset circuit activating power supply voltage VCC < 3V (hold for 10msec (Min)).

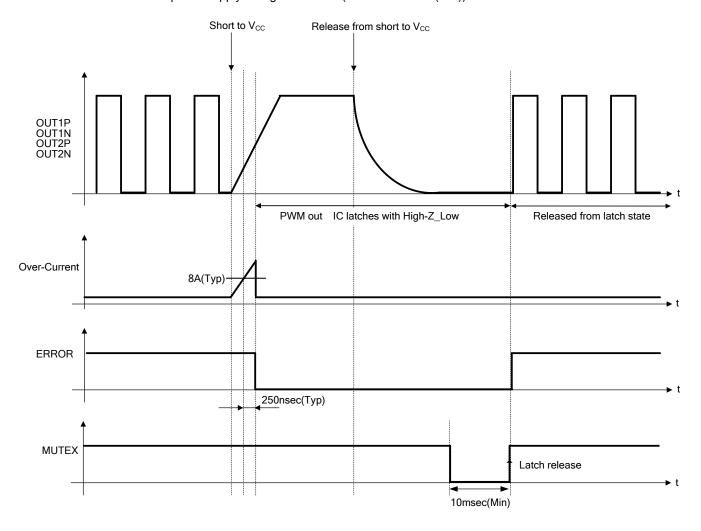


Figure 44. Output Short Protection Sequence (Short to Power Supply)

(2) Output Short Protection (Short to GND)

This IC has the PWM output short protection circuit that stops the PWM output when the output speaker (after LC-filter) is short-circuited to GND due to abnormality.

- Detecting condition It will detect when MUTEX pin is set High and the current that flows into the PWM output terminal becomes 8A(Typ) or more. If detected, the PWM output instantaneously goes to the state of High-Z_Low and IC is latched.
- Releasing method ① After turning MUTEX terminal to Low(holding time to Low = 10msec(Min)) turn back to High again.
 - ② Restore power supply after the voltage dropped to internal power on reset circuit activating power supply voltage VCC < 3V (hold for 10msec (Min)).</p>

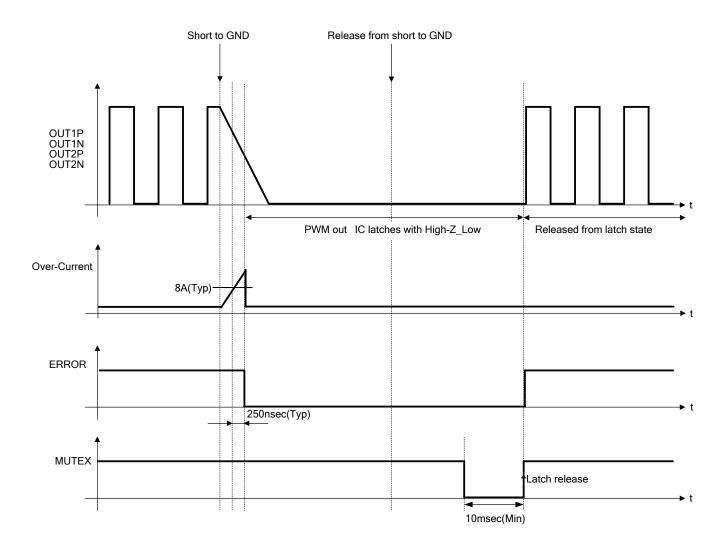


Figure 45. Sequence of the Output short protection (Short to GND)

(3) DC Voltage Protection

This IC is integrated with DC voltage protection circuit. When DC voltage is input to the speaker due to abnormality, speaker output will MUTE, and this protection will prevent the speaker from destruction.

Detecting condition - It will detect when MUTEX pin is set High and speaker output is more than 3.5V(Typ) over 0.33sec to 0.66sec.

Once detected, The PWM output instantaneously goes to the state of High-Z_Low, and IC will latch.

Releasing method -

- ① After turning MUTEX terminal to Low(holding time to Low = 10msec(Min)) turn back to High again.
- ② Restore power supply after the voltage dropped to internal power on reset circuit activating power supply voltage VCC < 3V (hold for 10msec (Min)).</p>

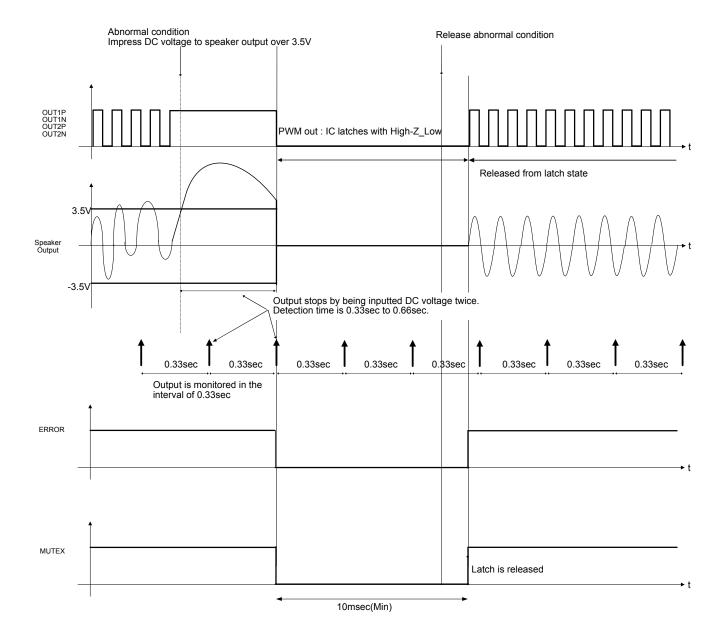


Figure 46. DC Voltage Protection Sequence

(4) Overheat Protection

This IC has the overheat protection circuit that prevents thermal runaway under an abnormal state for the chip temperature exceeded Tjmax=150°C.

Detecting condition - It will detect when MUTEX pin is set High and the temperature of the chip becomes 150°C (Typ) or more. Speaker output turns MUTE immediately, when High temperature protection is detected.

Releasing condition - It will release when MUTEX pin is set High and the temperature of the chip becomes 120°C (Typ) or less. The speaker output is outputted immediately when released. (Auto recovery)

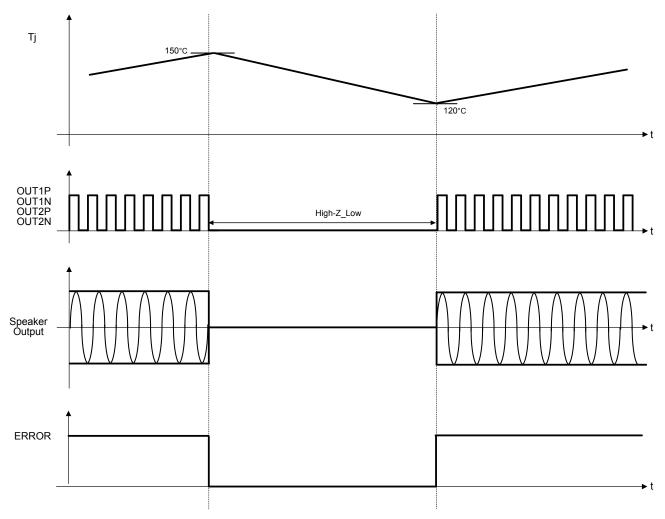


Figure 47. Overheat Protection Sequence

(5) Under Voltage Protection

This IC has the under voltage protection circuit that mutes the output speaker once extreme drop in the power supply voltage is detected.

Detecting condition - It will detect when MUTEX pin is set High and the power supply voltage becomes lower than 4V(Typ). Speaker output turn MUTE immediately when under voltage protection is detected.

Releasing condition - It will release when MUTEX pin is set High and the power supply voltage becomes more than 4.1V(Typ). The speaker output is outputted immediately when released. (Auto recovery)

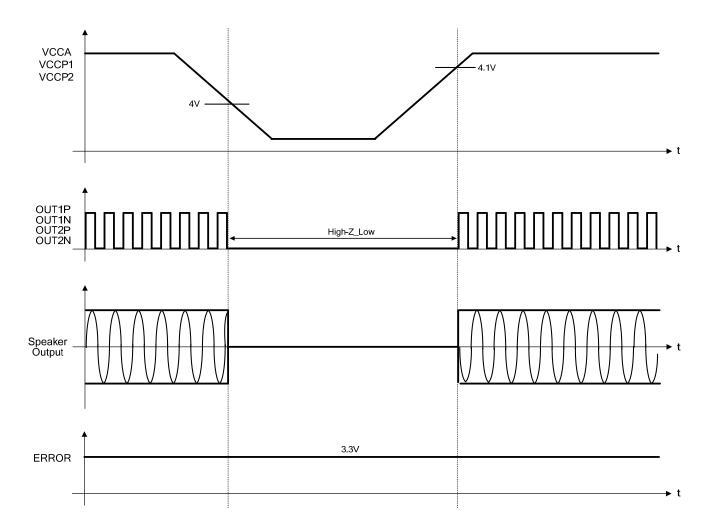


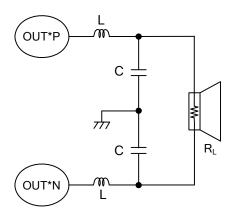
Figure 48. Under Voltage Protection Sequence

Selecting External Components

(1) Output LC Filter Circuit

An output filter is required to eliminate radio-frequency components exceeding the audio-frequency region supplied to a load (speaker). Because this IC uses output PWM frequencies any of 400kHz, 500kHz, or 600kHz, the high-frequency components must be appropriately removed.

This section takes an example of an LC type LPF shown below, in which coil L and capacitor C compose a differential filter with an attenuation property of -12dB/oct. A large part of switching currents flow to capacitor C, and only a small part of the currents flow to speaker R_L . This filter reduces unwanted emission this way. In addition, coil L and capacitor C compose a filter against in-phase components, reducing unwanted emission further.



The following shows output LC filter constants and cutoff frequencies f_C with typical load impedances.

R _L	L	С	f _C
4Ω	10µH	2.2µF	34kHz
6Ω, 8Ω	15µH	1µF	41kHz

Figure 49. Output LC Filter

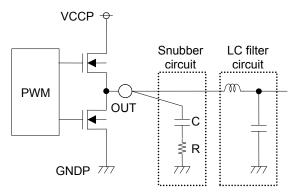
Use inductors with low ESR and with sufficient margin of allowable currents. Power loss will increase if inductors with high ESR are used.

Select a closed magnetic circuit type product in normal cases to prevent emission noise.

Use capacitors with low equivalent series resistance, and good impedance characteristics at high frequency ranges (100kHz or higher). Also, select an item with sufficient voltage rating because massive amount of high-frequency current flow is expected.

(2) Snubber circuit constant

When overshoot / undershoot of PWM Output exceeds absolute maximum rating, or when overshoot / undershoot of PWM output negatively affects EMC, snubber circuit is used as shown below. And if V_{CC}>11V, the snubber circuit must be added.



The following table shows ROHM recommended value of "Snubber filter constants" when using ROHM 4 layer board.

R_L	С	R
4Ω	680pF, 25V B(±10%)	5.6Ω, $1/10W J(±5%)$
6Ω	680pF, 25V B(±10%)	5.6Ω, $1/10W J(±5%)$
8Ω	680pF, 25V B(±10%)	5.6Ω, $1/10W J(±5%)$

Figure 50. Snubber circuit

Caution1: If the impedance characteristics of the speakers at high-frequency range increase rapidly, the IC might not have stable operation in the resonance frequency range of the LC filter. Therefore, consider adding damping-circuit, etc., depending on the impedance of the speaker.

Caution2: Though this IC has a short protection function, when short to VCC or GND after the LC filter, over current occurs during short protection function operation. Be careful about over/undershoot which exceeds the maximum standard ratings because back electromotive force of the inductor will occur which sometimes leads to IC destruction.

Power Dissipation

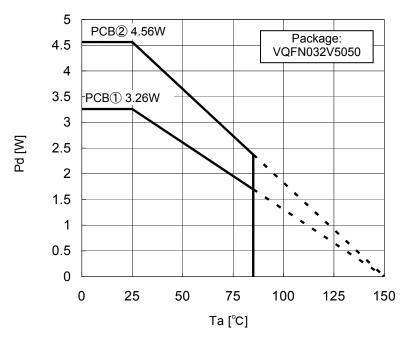


Figure 51. Power Dissipation vs Temperature

Measuring instrument: TH-156(Kuwano Electrical Instruments Co, Ltd.)

Measuring conditions: Installation on ROHM's board

Board size: 74.2mm x 74.2mm x 1.6mm(with thermal via on board)

Material: FR4

• The board on exposed heat sink on the back of package are connected by soldering.

PCB1: 4- layer board (Top and bottom layer back copper foil size: 20.2mm², 2nd and 3rd layer

back copper foil size: 5505mm^2), θ ja = 38.3°C/W PCB2: 4-layer board(back copper foil size: 5505mm^2), θ ja = 27.4°C/W

Use a thermal design that allows for a sufficient margin in consideration of power dissipation (Pd) under actual operating conditions. This IC exposes its frame of the backside of package. Note that this part is assumed to use after providing heat dissipation treatment to improve heat dissipation efficiency. Try to occupy as wide as possible with heat dissipation pattern not only on the board surface but also the backside.

Class D speaker amplifier has a high efficiency and low heat generation by comparison with conventional Analog power amplifier. However, In case it is operated continuously by maximum output power, Power dissipation (Pdiss) may exceed package dissipation. Please consider about heat design that Power dissipation (Pdiss) does not exceed Package dissipation (Pd) in average power (Poav).

Package dissipation : $Pd(W) = (Tjmax - Ta) / \theta ja$ Power dissipation : $Pdiss(W) = Poav x (1/\eta - 1)$

Where:

Tjmax is the maximum junction temperature=150°C, Ta is the peripheral temperature [°C] θ ja is the thermal resistance of package [°C /W] Poav is the average power [W] η is the efficiency

Operational Notes

1. Reverse Connection of Power Supply

Connecting the power supply in reverse polarity can damage the IC. Take precautions against reverse polarity when connecting the power supply, such as mounting an external diode between the power supply and the IC's power supply terminals.

2. Power Supply Lines

Design the PCB layout pattern to provide low impedance supply lines. Furthermore, connect a capacitor to ground at all power supply pins. Consider the effect of temperature and aging on the capacitance value when using electrolytic capacitors.

3. Ground Voltage

Ensure that no pins are at a voltage below that of the ground pin at any time, even during transient condition.

4. Ground Wiring Pattern

When using both small-signal and large-current ground traces, the two ground traces should be routed separately but connected to a single ground at the reference point of the application board to avoid fluctuations in the small-signal ground caused by large currents. Also ensure that the ground traces of external components do not cause variations on the ground voltage. The ground lines must be as short and thick as possible to reduce line impedance.

5. Thermal Consideration

Should by any chance the power dissipation rating be exceeded the rise in temperature of the chip may result in deterioration of the properties of the chip. In case of exceeding this absolute maximum rating, increase the board size and copper area to prevent exceeding the Pd rating.

6. Recommended Operating Conditions

These conditions represent a range within which the expected characteristics of the IC can be approximately obtained. The electrical characteristics are guaranteed under the conditions of each parameter.

7. Inrush Current

When power is first supplied to the IC, it is possible that the internal logic may be unstable and inrush current may flow instantaneously due to the internal powering sequence and delays, especially if the IC has more than one power supply. Therefore, give special consideration to power coupling capacitance, power wiring, width of ground wiring, and routing of connections.

8. Operation Under Strong Electromagnetic Field

Operating the IC in the presence of a strong electromagnetic field may cause the IC to malfunction.

9. Testing on Application Boards

When testing the IC on an application board, connecting a capacitor directly to a low-impedance output pin may subject the IC to stress. Always discharge capacitors completely after each process or step. The IC's power supply should always be turned off completely before connecting or removing it from the test setup during the inspection process. To prevent damage from static discharge, ground the IC during assembly and use similar precautions during transport and storage.

10. Inter-pin Short and Mounting Errors

Ensure that the direction and position are correct when mounting the IC on the PCB. Incorrect mounting may result in damaging the IC. Avoid nearby pins being shorted to each other especially to ground, power supply and output pin. Inter-pin shorts could be due to many reasons such as metal particles, water droplets (in very humid environment) and unintentional solder bridge deposited in between pins during assembly to name a few.

11. Unused Input Terminals

Input terminals of an IC are often connected to the gate of a MOS transistor. The gate has extremely high impedance and extremely low capacitance. If left unconnected, the electric field from the outside can easily charge it. The small charge acquired in this way is enough to produce a significant effect on the conduction through the transistor and cause unexpected operation of the IC. So unless otherwise specified, unused input terminals should be connected to the power supply or ground line.

Operational Notes - continued

12. Regarding Input Pins of the IC

This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P-N junctions are formed at the intersection of the P layers with the N layers of other elements, creating a parasitic diode or transistor. For example (refer to figure below):

When GND > Pin A and GND > Pin B, the P-N junction operates as a parasitic diode.

When GND > Pin B, the P-N junction operates as a parasitic transistor.

Parasitic diodes inevitably occur in the structure of the IC. The operation of parasitic diodes can result in mutual interference among circuits, operational faults, or physical damage. Therefore, conditions that cause these diodes to operate, such as applying a voltage lower than the GND voltage to an input pin (and thus to the P substrate) should be avoided.

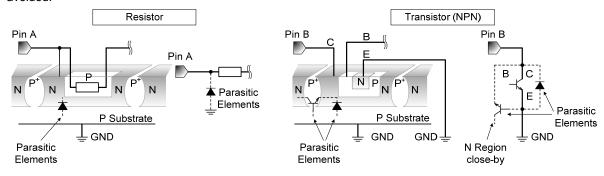


Figure 52. Example of Monolithic IC Structure

13. Ceramic Capacitor

When using a ceramic capacitor, determine the dielectric constant considering the change of capacitance with temperature and the decrease in nominal capacitance due to DC bias and others.

14. Thermal Shutdown Circuit (TSD)

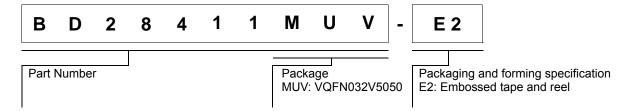
This IC has a built-in thermal shutdown circuit that prevents heat damage to the IC. Normal operation should always be within the IC's power dissipation rating. If however the rating is exceeded for a continued period, the junction temperature (Tj) will rise which will activate the TSD circuit that will turn OFF all output pins. When the Tj falls below the TSD threshold, the circuits are automatically restored to normal operation.

Note that the TSD circuit operates in a situation that exceeds the absolute maximum ratings and therefore, under no circumstances, should the TSD circuit be used in a set design or for any purpose other than protecting the IC from heat damage.

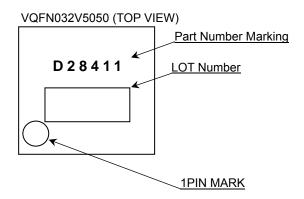
15. Over Current Protection Circuit (OCP)

This IC has a built-in overcurrent protection circuit that activates when the output is accidentally shorted. However, it is strongly advised not to subject the IC to prolonged shorting of the output.

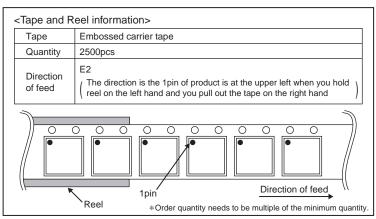
Ordering Information



Marking Diagram



Datasheet BD28411MUV Physical Dimension, Tape and Reel Information Package Name VQFN032V5050 5. 0 ± 0.1 $0 \pm 0.$ 1 3 Q 1PIN MARK OMAX ____ 22) 03 0 2 +0. □ 0. 08S (0) C0. 2 3. 4 ± 0.1 32 4 ± 0 . 0 25 16 $\mathsf{n}\mathsf{n}\mathsf{n}\mathsf{n}\mathsf{n}\mathsf{n}\mathsf{n}$ (UNIT:mm) 24 PKG: VQFN032V5050 $0.\ 25^{\ +0.\ 05}_{\ -0.\ 04}$ 0. 5 0.75 Drawing No. EX461-5001-2



Revision History

Date	Revision	Changes
29.Oct.2014	001	First version

Notice

Precaution on using ROHM Products

1. Our Products are designed and manufactured for application in ordinary electronic equipments (such as AV equipment, OA equipment, telecommunication equipment, home electronic appliances, amusement equipment, etc.). If you intend to use our Products in devices requiring extremely high reliability (such as medical equipment (Note 1), transport equipment, traffic equipment, aircraft/spacecraft, nuclear power controllers, fuel controllers, car equipment including car accessories, safety devices, etc.) and whose malfunction or failure may cause loss of human life, bodily injury or serious damage to property ("Specific Applications"), please consult with the ROHM sales representative in advance. Unless otherwise agreed in writing by ROHM in advance, ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of any ROHM's Products for Specific Applications.

(Note1) Medical Equipment Classification of the Specific Applications

JÁPAN	JÁPAN USA		CHINA
CLASSII		CLASSIIb	OL ACOM
CLASSIV	CLASSⅢ	CLASSⅢ	CLASSⅢ

- 2. ROHM designs and manufactures its Products subject to strict quality control system. However, semiconductor products can fail or malfunction at a certain rate. Please be sure to implement, at your own responsibilities, adequate safety measures including but not limited to fail-safe design against the physical injury, damage to any property, which a failure or malfunction of our Products may cause. The following are examples of safety measures:
 - [a] Installation of protection circuits or other protective devices to improve system safety
 - [b] Installation of redundant circuits to reduce the impact of single or multiple circuit failure
- 3. Our Products are designed and manufactured for use under standard conditions and not under any special or extraordinary environments or conditions, as exemplified below. Accordingly, ROHM shall not be in any way responsible or liable for any damages, expenses or losses arising from the use of any ROHM's Products under any special or extraordinary environments or conditions. If you intend to use our Products under any special or extraordinary environments or conditions (as exemplified below), your independent verification and confirmation of product performance, reliability, etc, prior to use, must be necessary:
 - [a] Use of our Products in any types of liquid, including water, oils, chemicals, and organic solvents
 - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
 - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl₂, H₂S, NH₃, SO₂, and NO₂
 - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
 - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
 - [f] Sealing or coating our Products with resin or other coating materials
 - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
 - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation (Pd) depending on Ambient temperature (Ta). When used in sealed area, confirm the actual ambient temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

Precautions Regarding Application Examples and External Circuits

- If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
- You agree that application notes, reference designs, and associated data and information contained in this document are presented only as guidance for Products use. Therefore, in case you use such information, you are solely responsible for it and you must exercise your own independent verification and judgment in the use of such information contained in this document. ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of such information.

Precaution for Electrostatic

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of Ionizer, friction prevention and temperature / humidity control).

Precaution for Storage / Transportation

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
 - [a] the Products are exposed to sea winds or corrosive gases, including Cl2, H2S, NH3, SO2, and NO2
 - [b] the temperature or humidity exceeds those recommended by ROHM
 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

Precaution for Product Label

QR code printed on ROHM Products label is for ROHM's internal use only.

Precaution for Disposition

When disposing Products please dispose them properly using an authorized industry waste company.

Precaution for Foreign Exchange and Foreign Trade act

Since our Products might fall under controlled goods prescribed by the applicable foreign exchange and foreign trade act, please consult with ROHM representative in case of export.

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